# MEMORY CELL LAYOUT AND PROCESS FLOW

## ABSTRACT

A memory device (10) comprises an active area (16) comprising a source (20) and at least two drains (18) defining a first axis (A-A). At least two substantially parallel word lines (12) are defined by a first pitch, with one word line (12) located between each drain (18) and the source (20). Digit lines (14) are defined by a second pitch, one of the digit lines (14) being coupled to the source (20) and forming a second axis (B-B). The active areas (16) of the memory array are tilted at 45° to the grid defined by the word lines (12) and digit lines (14). The word line pitch is about 1.5F, while the digit line pitch is about 3F.

FIGURE 1